

**In the Claims:**

Please add new claims 21-23. The claims are as follows.

1. (Original) A method for controlling a process on a substrate comprising:  
    providing the substrate, the substrate having an upper surface, an opposite lower surface  
    and an edge between the upper and lower surfaces;  
    processing the upper surface of the substrate with a first fluid;  
    directing a second fluid against a portion of the lower surface proximate to the edge of the  
    substrate, wherein said second fluid flows adjacent to the edge of the substrate; and  
    controlling the temperature of said second fluid in order to affect a processing of an edge  
    region of the upper side of the substrate.
2. (Original) The method of claim 1, wherein the substrate is a semiconductor wafer.
3. (Original) The method of claim 1, wherein the second fluid comprises a gas.
4. (Original) The method of claim 3, wherein the gas is selected from the group consisting of  
nitrogen, argon, helium and compressed air.
5. (Original) The method of claim 1 wherein the step of controlling the temperature of said  
second fluid comprises increasing the temperature of the second fluid above an ambient

temperature.

6. (Original) The method of claim 5, wherein the step of processing the upper surface of the substrate comprises etching said upper surface and wherein increasing the temperature of said second fluid causes the etch rate of the processing to increase.

7. (Original) The method of claim 1 wherein the step of controlling the temperature of said second fluid comprises decreasing the temperature of the second fluid below an ambient temperature.

8. (Original) The method of claim 7, wherein the step of processing the upper surface of the substrate comprises etching said upper surface and wherein decreasing the temperature of said second fluid causes the etch rate of the processing to decrease.

9. (Original) The method of claim 1, wherein the substrate is elevated above a Bernoulli chuck.

10. (Original) The method of claim 12, wherein said Bernoulli chuck uses said second fluid to elevate the substrate.

11. (Original) The method of claim 1, wherein the step of processing the upper side of the substrate with said first fluid is performed at ambient pressure.

12. (Original) The method of claim 1, further including rotating the substrate.

13. (Original) A method for processing a substrate having an upper surface, an opposite lower surface and an edge between the upper and lower surfaces, comprising:

providing a chuck for elevating the substrate above an upper surface of said chuck using a suspension fluid, said suspension fluid delivered from an annular opening in said upper surface of said chuck, said annular opening located proximate to an edge of said chuck, said suspension fluid in contact with the lower surface of the substrate proximate to the edge of the substrate;

delivering a processing fluid to the upper surface of the substrate; and

maintaining the temperature of said suspension fluid at a temperature different from an ambient temperature while delivering said processing fluid.

14. (Original) The method of claim 13, wherein temperature of said suspension fluid is maintained above or below the ambient temperature.

15. (Original) The method of claim 13, further including:

sensing the temperature of said suspension fluid proximate to said annular opening; and

controlling the temperature of said suspension fluid proximate to said annular opening to a predetermined value.

16. (Original) The method of claim 13, further including rotating said chuck.

17-20. (Canceled)

21. (New) The method of claim 1, further comprising a temperature sensor that measures the temperature of the second fluid near the edge of the substrate.

22. (New) The method of claim 21, further comprising a controller for displaying the temperature measured by the temperature sensor, said controller being electrically connected to the temperature sensor.

23. (New) The method of claim 22, wherein controlling the temperature of the second fluid comprises heating or cooling the second fluid by a thermal device that is electrically connected to the controller, said thermal device being a heater or a chiller.